

HiPerFRED²

DPF80C200HB

preliminary

V_{RRM}	=	200 V
I _{fav}	<i>=</i> 2x	40 A
t _{rr}	=	55 ns

High Performance Fast Recovery Diode Low Loss and Soft Recovery Common Cathode

Part number

DPF80C200HB



Package: TO-247

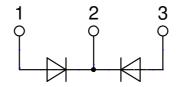
RoHS compliant

• Industry standard outline

• Epoxy meets UL 94V-0

Backside: cathode

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Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
 Soft reverse recovery for low EMI/RFI
- Soll reverse recover
 Low Irm reduces:
- Power dissipation within the diode
- Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

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Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blocki	ng voltage	$T_{VJ} = 25^{\circ}C$			200	V
V _{RRM}	max. repetitive reverse blocking vo	bltage	$T_{v_J} = 25^{\circ}C$			200	V
I _R	reverse current, drain current	V_{R} = 200 V	$T_{VJ} = 25^{\circ}C$			1	μA
		$V_{R} = 200 V$	$T_{vJ} = 150^{\circ}C$			0.2	mA
V _F	forward voltage drop	I _F = 40 A	$T_{vJ} = 25^{\circ}C$			1.22	V
		I _F = 80 A				1.45	V
		$I_{F} = 40 \text{ A}$	T _{vJ} = 150°C			0.95	V
		I _F = 80 A				1.20	V
I FAV	average forward current	$T_c = 145^{\circ}C$	$T_{vJ} = 175^{\circ}C$			40	А
		rectangular d = 0.5					
V _{F0}	threshold voltage		T _{vJ} = 175°C			0.67	V
r _F	slope resistance } for power lo	ss calculation only				5.8	mΩ
\mathbf{R}_{thJC}	thermal resistance junction to case	2				0.7	K/W
\mathbf{R}_{thCH}	thermal resistance case to heatsin	k			0.3		K/W
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$			215	W
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; $V_{R} = 0 V$	$T_{VJ} = 45^{\circ}C$			560	Α
C	junction capacitance	$V_{R} = 100 V f = 1 MHz$	$T_{v_J} = 25^{\circ}C$		81		pF
I _{RM}	max. reverse recovery current		$T_{vJ} = 25 °C$		6		А
		$I_F = 40 \text{ A}; V_R = 100 \text{ V}$	$T_{vJ} = 125 ^{\circ}C$		11		Α
t _{rr}	reverse recovery time	I _F = 40 A; V _R = 100 V -di _F /dt = 200 A/μs	$T_{vJ} = 25 °C$		55		ns
	J		$T_{vJ} = 125 ^{\circ}C$		85		ns

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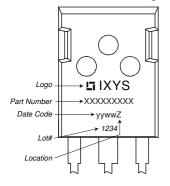


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Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal 1)			70	А
T _{vj}	virtual junction temperature		-55		175	°C
T _{op}	operation temperature		-55		150	°C
T _{stg}	storage temperature		-55		150	°C
Weight				6		g
M _D	mounting torque		0.8		1.2	Nm
F _c	mounting force with clip		20		120	Ν

Product Marking



Part description

- D = Diode
- P = HiPerFRED F = ultra fast
- 80 = Current Rating [A]
- C = Common Cathode
- 200 = Reverse Voltage [V]HB = TO-247AD (3)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DPF80C200HB	DPF80C200HB	Tube	30	508214

Similar Part	Package	Voltage class
DPF60C200HJ	ISOPLUS247 (3)	200

Equivalent Circuits for Simulation		* on die level	$T_{VJ} = 175^{\circ}C$	
)[R]-	Fast Diode		
V _{0 max}	threshold voltage	0.67		V
$\mathbf{R}_{0 \max}$	slope resistance *	3.2		mΩ

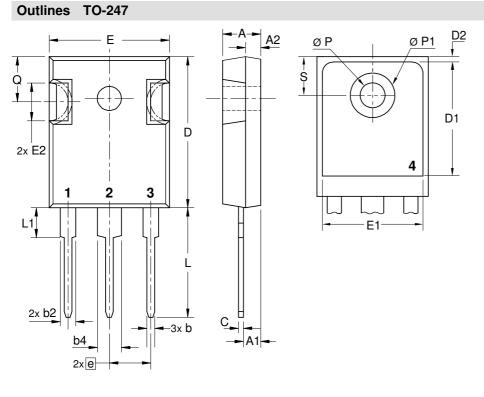
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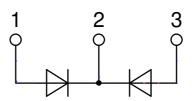


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Sym.	Inches		Millim	eter
	min.	max.	min.	max.
Α	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
е	0.215	BSC	5.46	BSC
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
ØР	0.140	0.144	3.55	3.65
Q	0.212	0.244	5.38	6.19
S	0.242	BSC	6.14	BSC
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
с	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
Ø P1	-	0.29	-	7.39



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